

MS2473

600 Watts, 50 Volts, Pulsed Avionics 1090 MHz

GENERAL DESCRIPTION

The MS2473 is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems in the 1090MHz frequency band. The device has gold thin-film metallization for proven highest MTTF. Low thermal resistance packaging reduces the junction temperature and extends device lifetime.

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C² 2300 Watts

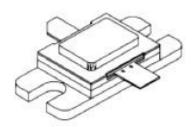
Maximum Voltage and Current

BVcboCollector to Base Voltage65 VoltsBVeboEmitter to Base Voltage3.5 VoltsIcCollector Current46 Amps

Maximum Temperatures

Storage Temperature $-65 \text{ to} + 150^{\circ}\text{C}$ Operating Junction Temperature $+200^{\circ}\text{C}$

CASE OUTLINE M112



.400 x .500 2LFL (M112) hermetically sealed

ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout Pin Pg ¶c RL _{IN}	Power Out Power Input = 150W Power Gain Collector Efficiency Input Return Loss	F = 1090 MHz Vcc = 50 Volts PW = 10 μsec DF = 1% F = 1090 MHz	600 6.0 35 10	150		Watts Watts dB % dB

BVebo BVcbo	Emitter to Base Breakdown Collector to Base Breakdown	Ie = 10 mA Ic = 25 mA	3.5 65			Volts Volts
Ices	Collector to Emitter Leakage	Vce = 50V			35	mA
h _{FE}	DC - Current Gain	Vce = 5V, Ic = 1A	5		200	
Θjc^2	Thermal Resistance			0.06		C/W

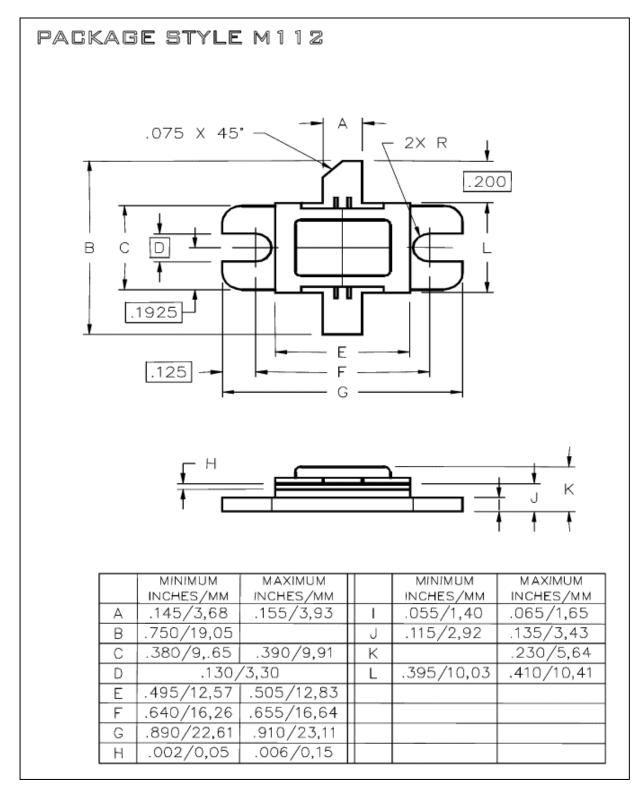
Note 1: At rated output power and pulse conditions

2: At rated pulse conditions

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